

4.(Original) A high-frequency circuit board unit according to one of claims 2 and 3, wherein said passive impedance circuit device is formed on a dielectric substrate having a dielectric constant higher than that of both said circuit board and said semiconductor device.

5.(Original) A high-frequency circuit board unit according to one of claims 2 and 3, wherein said semiconductor device is bump-mounted on said circuit board.

6. (Original) A high-frequency circuit board unit according to any one of claims 1 to 3, further comprising an additional terminal other than said high-frequency signal terminal on said semiconductor device, and an electrostatic protecting diode connected to said additional terminal.

7.(Original) A high-frequency module comprising said high-frequency circuit board unit set forth in any one of claims 1 to 3, further comprising an additional component mounted on said circuit board, a cover on said circuit board, and said terminal electrode being disposed externally of said cover.

8.(Original) An electronic apparatus comprising said high-frequency module set forth in claim 7.

9. (Original) An electronic apparatus comprising said high-frequency circuit board unit set forth in any one of claims 1 to 3.

10.(Currently Amended) A manufacturing method for a high-frequency circuit board unit, the manufacturing method comprising ~~the steps of~~:

mounting, on a circuit board including a ground electrode and a terminal electrode, a passive impedance circuit device, at least one terminal of which is connected to said ground electrode for conducting direct current, in such a manner that said at least one terminal is connected to said terminal electrode; and

mounting a semiconductor device including a high-frequency signal terminal and a non-high-frequency signal terminal on said circuit board in such a manner that said high-frequency signal terminal is connected to the other terminal of said passive impedance circuit device and said non-high-frequency signal terminal does not send or receive a high-frequency signal.

11.(Original) A manufacturing method for a high-frequency circuit board unit according to claim 10, wherein said passive impedance circuit device and said semiconductor device are bump-mounted on said circuit board.

12.(Original) A manufacturing method according to claim 10, wherein said at least one terminal of said passive impedance circuit device is connected to said ground electrode after said semiconductor device is mounted on said circuit board.

13.(Original) A manufacturing method according to claim 12, wherein said at least one terminal of said passive impedance circuit device is connected to said ground electrode before said high-frequency signal terminal is connected to said other terminal of said passive impedance circuit device.